2SK3673-01MR

200304

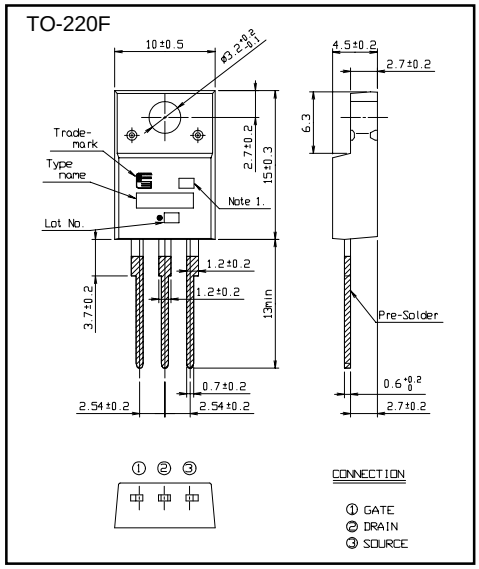
FUJI POWER MOSFET
Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

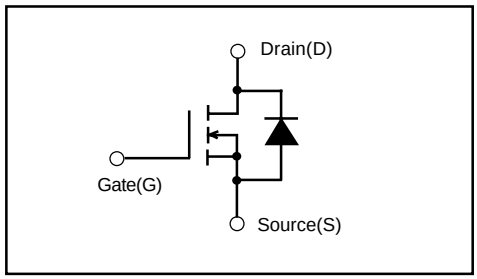
■ Features
- High speed switching
- Low on-resistance
- No secondary breadown
- Low driving power
- Avalanche-proof

■ Applications
- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

■ Outline Drawings [mm]



■ Equivalent circuit schematic



■ Maximum ratings and characteristicAbsolute maximum ratings

● (Tc=25°C unless otherwise specified)

Item	Symbol		Ratings	Unit
Drain-source voltage	V_{DS}		700	V
	V_{DSX} *5		700	V
Continuous drain current	I_D		±10	A
Pulsed drain current	$I_{D(puls)}$		±40	A
Gate-source voltage	V_{GS}		±30	V
Repetitive or non-repetitive	I_{AR} *2		10	A
Maximum Avalanche Energy	E_{AS} *1		242.2	mJ
Maximum Drain-Source dV/dt	dV_{DS}/dt *4		40	kV/µs
Peak Diode Recovery dV/dt	dV/dt *3		5	kV/µs
Max. power dissipation	P_D	Ta=25°C	2.16	W
		Tc=25°C	80	
Operating and storage temperature range	T_{ch}		+150	℃
	T_{stg}		-55 to +150	℃
Isolation Voltage	V_{iso} *6		2	kVrms

*1 L=4.45mH, Vcc=70V,Tch=25°C, See to Avalanche Energy Graph *2 Tch≦150°C
*3 I_F≦-I_D, -di/dt=50A/µs, Vcc≦BV_{DSS}, Tch≦150°C *4 V_{DS}≦700V *5 V_{GS}=-30V *6 t=60sec, f=60Hz

● Electrical characteristics (T_C =25°C unless otherwise specified)

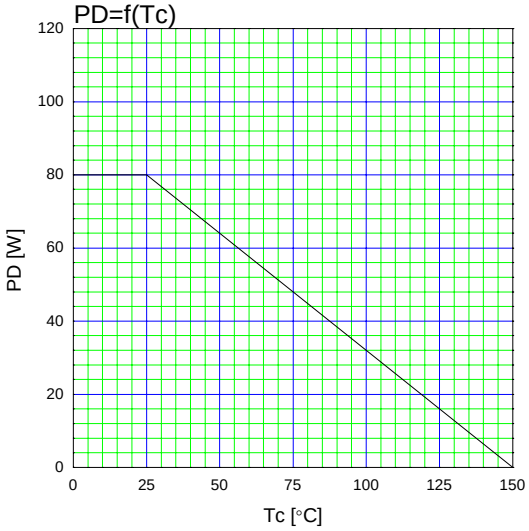
Item	Symbol	Test Conditions		Min.	Typ.	Max.	Units
Drain-source breakdown voltaget	$V_{(BR)DSS}$	I_D=250µA V_{GS}=0V		700			V
Gate threshold voltage	$V_{GS(th)}$	I_D= 250µA V_{DS}=V_{GS}		3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=700V V_{GS}=0V	Tch=25°C			25	µA
		V_{DS}=560V V_{GS}=0V	Tch=125°C			250	
Gate-source leakage current	I_{GSS}	V_{GS}=±30V V_{DS}=0V				100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=5A V_{GS}=10V			0.91	1.18	Ω
Forward transcondutance	gfs	I_D=5A V_{DS}=25V		5	9.5		S
Input capacitance	Ciss	V_{DS}=25V			900	1350	pF
Output capacitance	Coss	V_{GS}=0V			140	210	
Reverse transfer capacitance	Crss	f=1MHz			8	12	
Turn-on time ton	td(on)	V_{CC}=300V I_D=5A			22	33	ns
	tr	V_{GS}=10V			6	9	
Turn-off time toff	td(off)	R_{GS}=10 Ω			40	60	
	tf				9	14	
Total Gate Charge	Q_G	V_{CC}=350V			25	37.5	nC
Gate-Source Charge	Q_{GS}	I_D=10A			4	6	
Gate-Drain Charge	Q_{GD}	V_{GS}=10V			8.5	13	
Avalanche capability	I_{AV}	L=4.45mH Tch=25°C		10			A
Diode forward on-voltage	V_{SD}	I_F=10A V_{GS}=0V Tch=25°C			0.90	1.50	V
Reverse recovery time	trr	I_F=10A V_{GS}=0V			2.75		µs
Reverse recovery charge	Qrr	-di/dt=100A/µs Tch=25°C			14.0		µC

● Thermalcharacteristics

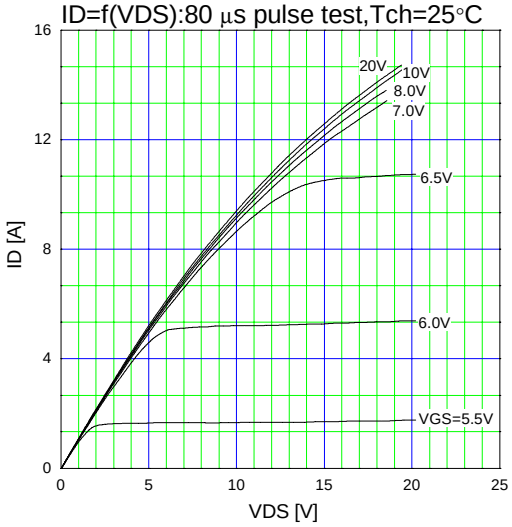
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			1.563	°C/W
	$R_{th(ch-a)}$	channel to ambient			58.0	°C/W

Characteristics

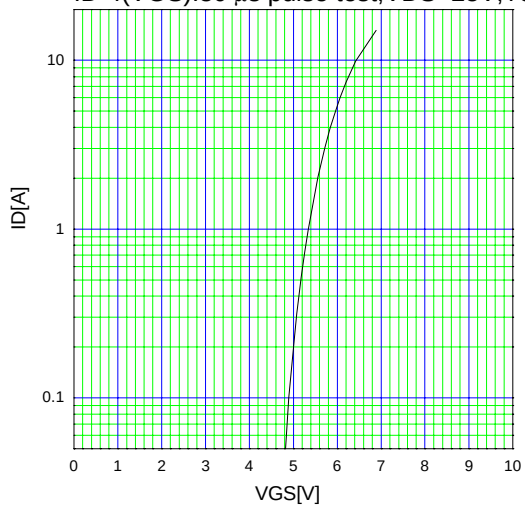
Allowable Power Dissipation
PD=f(Tc)



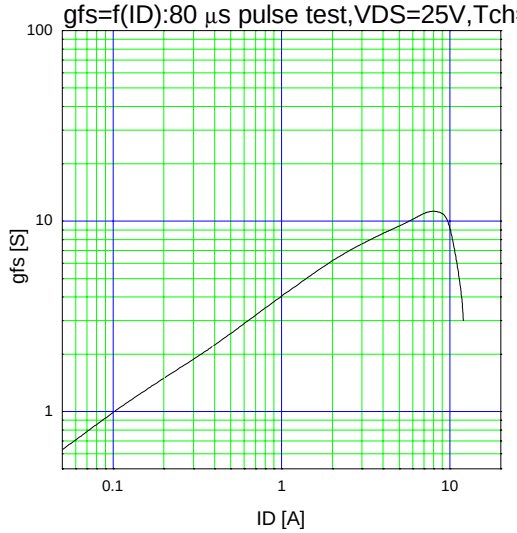
Typical Output Characteristics
ID=f(VDS):80 μs pulse test,Tch=25°C



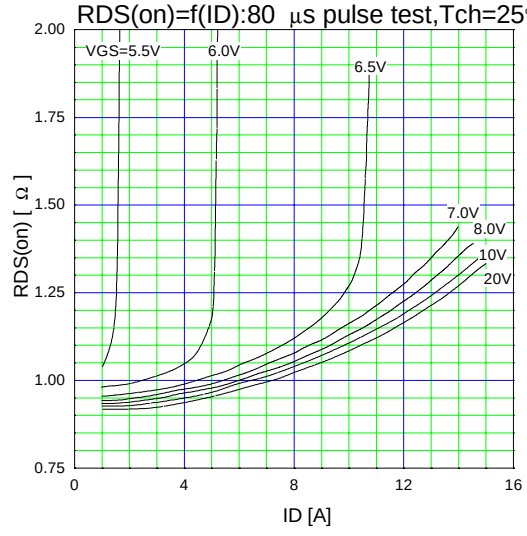
Typical Transfer Characteristic
ID=f(VGS):80 μs pulse test,VDS=25V,Tch=25°C



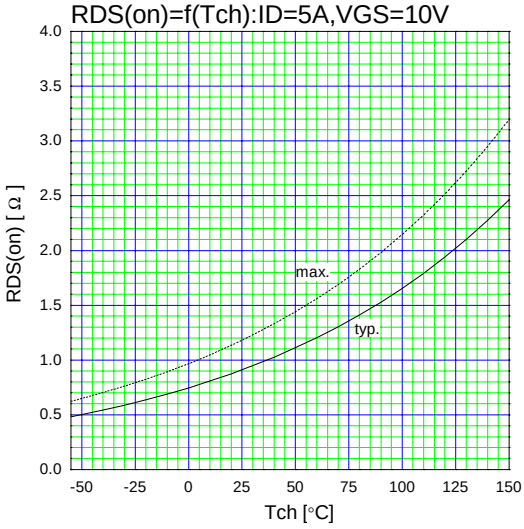
Typical Transconductance
gfs=f(ID):80 μs pulse test,VDS=25V,Tch=25°C



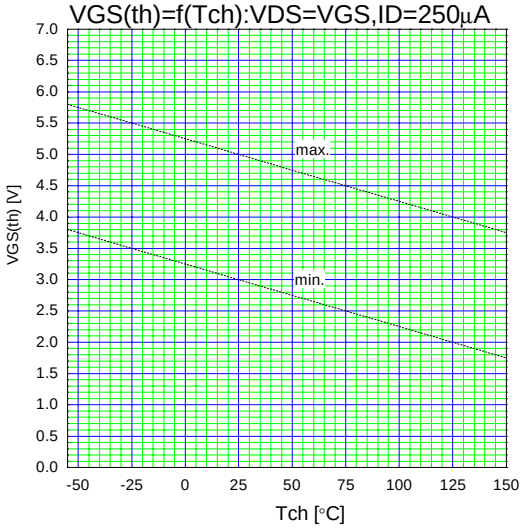
Typical Drain-Source on-state Resistance
RDS(on)=f(ID):80 μs pulse test,Tch=25°C



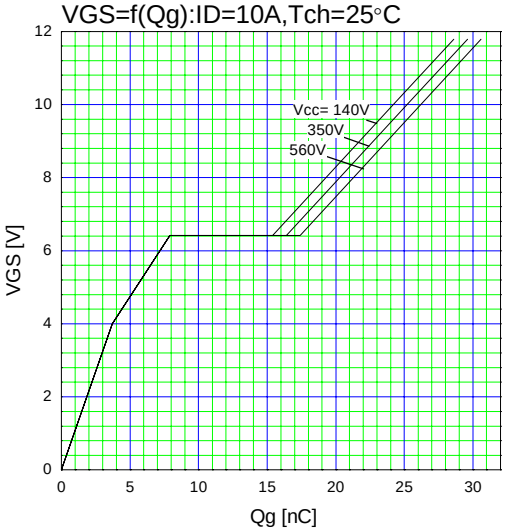
Drain-Source On-state Resistance
RDS(on)=f(Tch):ID=5A,VGS=10V



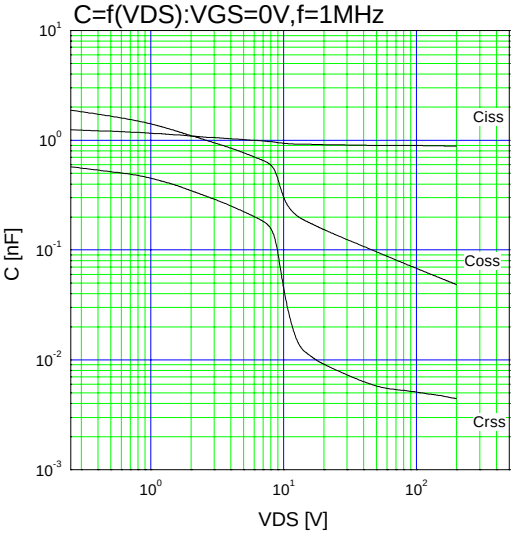
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch):VDS=VGS,ID=250μA



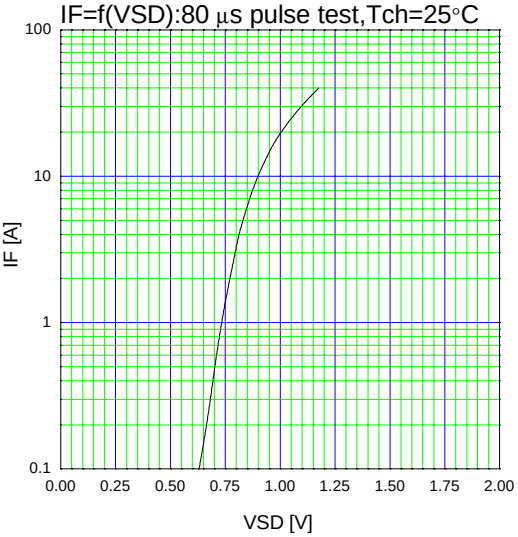
Typical Gate Charge Characteristics
VGS=f(Qg):ID=10A,Tch=25°C



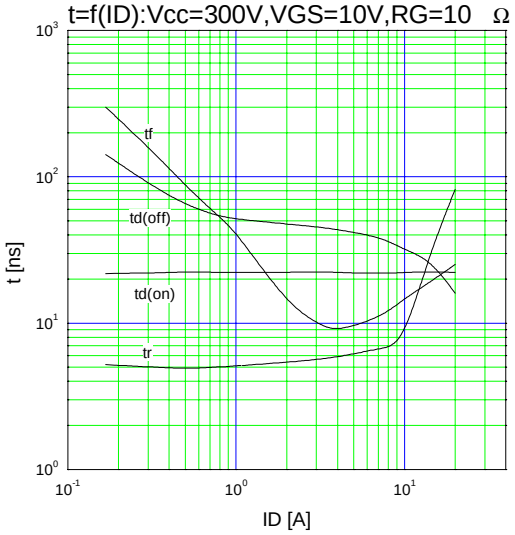
Typical Capacitance
C=f(VDS):VGS=0V,f=1MHz



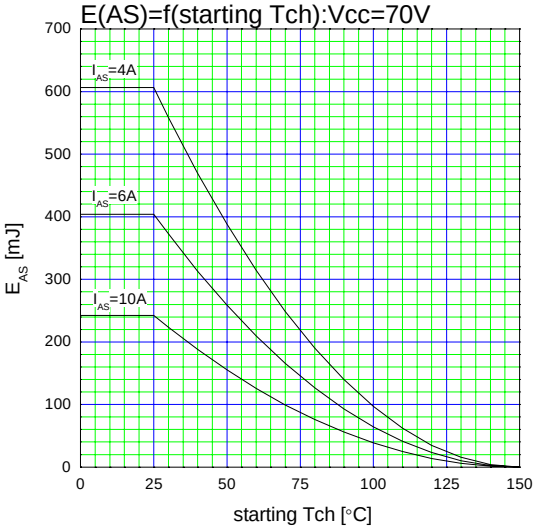
Typical Forward Characteristics of Reverse Diode
IF=f(VSD):80 μs pulse test,Tch=25°C



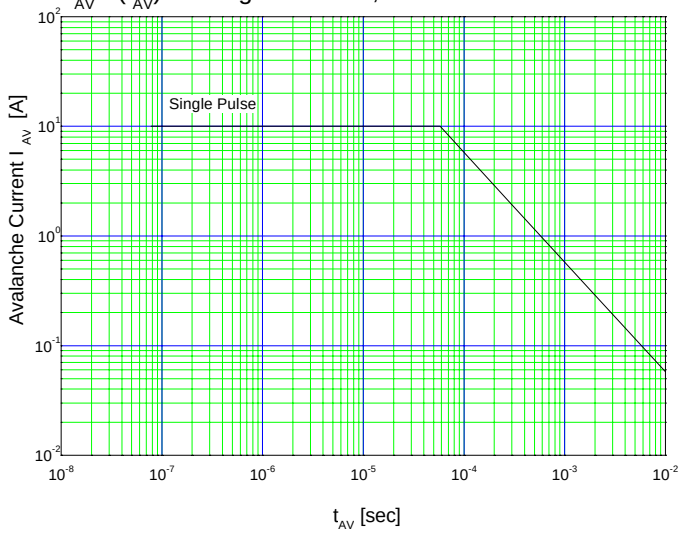
Typical Switching Characteristics vs. ID
t=f(ID):Vcc=300V,VGS=10V,RG=10 Ω



Maximum Avalanche Energy vs. starting Tch
E(AS)=f(starting Tch):Vcc=70V



Maximum Avalanche Current Pulsewidth
I_{AV}=f(t_{AV}):starting Tch=25°C,Vcc=70V



Maximum Transient Thermal Impedance
Zth(ch-c)=f(t):D=0